查询1SV313供应商

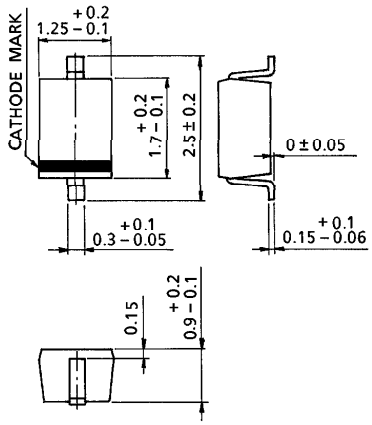
TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1 S V 3 1 3

VCO FOR UHF BAND RADIO

Unit in mm

- High Capacitance Ratio : $C_{0.5\,V} / C_{2.5\,V} = 2.5$ (Typ.)
- Low Series Resistance : $r_s = 0.35\ \Omega$ (Typ.)
- Useful for Small Size Tuner



USC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1E1A

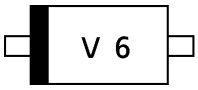
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 1\ \mu A$	10	—	—	V
Reverse Current	I_R	$V_R = 10$ V	—	—	3	nA
Capacitance	$C_{0.5\,V}$	$V_R = 0.5$ V, f = 1 MHz	7.3	—	8.4	pF
Capacitance	$C_{2.5\,V}$	$V_R = 2.5$ V, f = 1 MHz	2.75	—	3.4	pF
Capacitance Ratio	$C_{0.5\,V} / C_{2.5\,V}$	—	2.4	2.5	—	—
Series Resistance	r_s	$V_R = 1$ V, f = 470 MHz	—	0.35	—	Ω

MARKING



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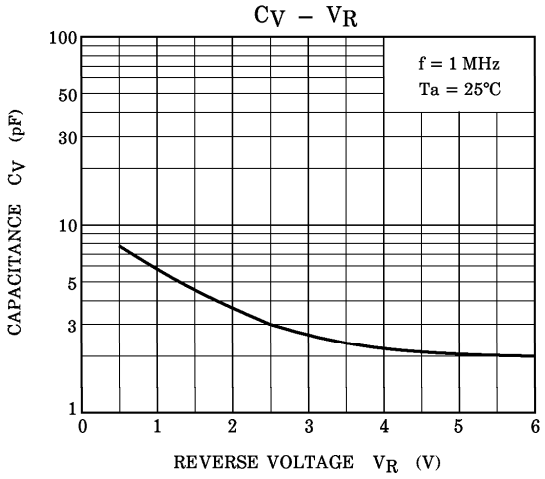
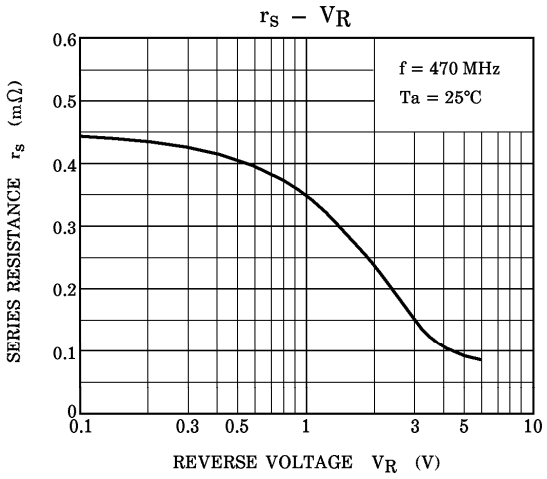

$C_V - V_R$
f = 1 MHz
Ta = 25°C
CAPACITANCE C_V (pF)
100
50
30
10
5
3
1
0
1
2
3
4
5
6
REVERSE VOLTAGE V_R (V)


$r_S - V_R$
f = 470 MHz
Ta = 25°C
SERIES RESISTANCE r_S (mΩ)
0.6
0.5
0.4
0.3
0.2
0.1
0
0.1
0.3
0.5
1
3
5
10
REVERSE VOLTAGE V_R (V)